

N-channel 200V 5.8mΩ Power MOSFET

Description

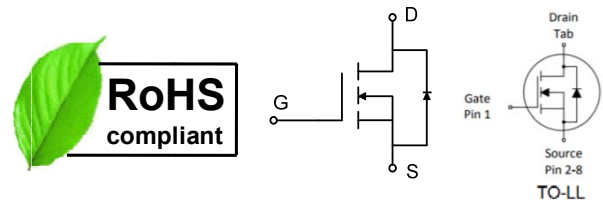
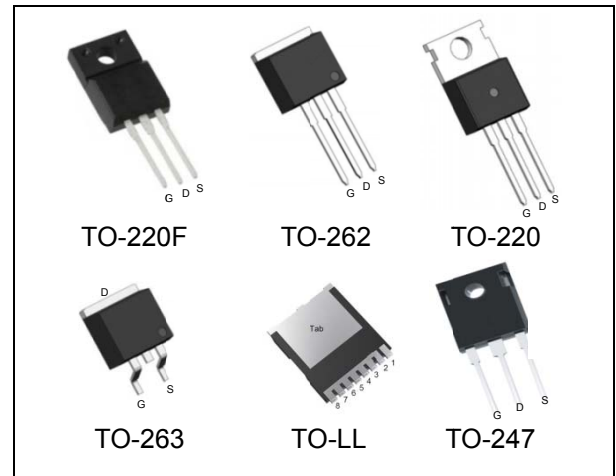
WMOS™ JNM is suitable for applications which require superior power density and outstanding efficiency.

Features

- Gate charge minimized
- Typ. $R_{DS(on)} = 5.8m\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

Switching applications



Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Drain-source voltage	V_{DS}	200		V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	145		A
($T_C = 100^\circ C$)		87		A
Pulsed drain current ²⁾	I_{DM}	435		A
Gate-source voltage	V_{GS}	± 20		V
Avalanche energy, single pulse ³⁾	E_{AS}	700		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	0.3		mJ
Avalanche current, repetitive ²⁾	I_{AR}	5		A
Power dissipation ($T_C = 25^\circ C$)	P_D	312	35	W
- Derate above $25^\circ C$		2.5	0.28	W/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		$^\circ C$
Continuous diode forward current	I_S	145		A
Diode pulse current	$I_{S,pulse}$	435		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.4	3.6	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =1 mA	200	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2.5	3.5	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =200 V, V _{GS} =0V, T _J = 25°C T _J = 125°C	- -	- 100	10 -	μA
Gate leakage current, forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V	-	-	500	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =30A T _J = 25°C	- -	 5.8	 7	 mΩ
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 100V, V _{GS} = 0V, f = 1 MHz	-	6788	-	pF
Output capacitance	C _{oss}		-	236	-	
Reverse transfer capacitance	C _{rss}		-	38	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 100V, I _D = 30A R _G = 4.7Ω, V _{GS} =10V	-	16	-	ns
Rise time	t _r		-	31	-	
Turn-off delay time	t _{d(off)}		-	155	-	
Fall time	t _f		-	5	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =160V, I _D =30A, V _{GS} =0 to 10V	-	32	-	nC
Gate to drain charge	Q _{gd}		-	24	-	
Gate charge total	Q _g		-	121	-	
Gate plateau voltage	V _{plateau}		-	5.0	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =30A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50V, I _F =30A, dI _F /dt=100A/μs	-	120	-	ns
Reverse recovery charge	Q _{rr}		-	0.6	-	μC
Peak reverse recovery current	I _{rrm}		-	8	-	A

Notes:

- Limited by $T_{j\max}$. Maximum duty cycle $D=0.5$.
- Repetitive rating: pulse width limited by maximum junction temperature.
- $I_{AS}=5\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, starting $T_j=25^\circ\text{C}$.

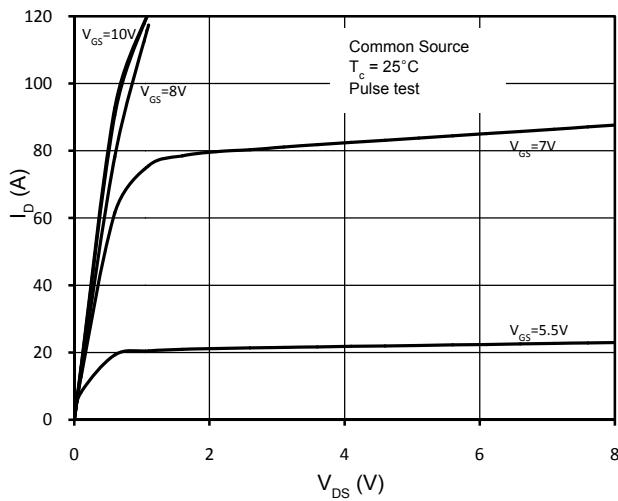


Figure 1. On-Region Characteristics

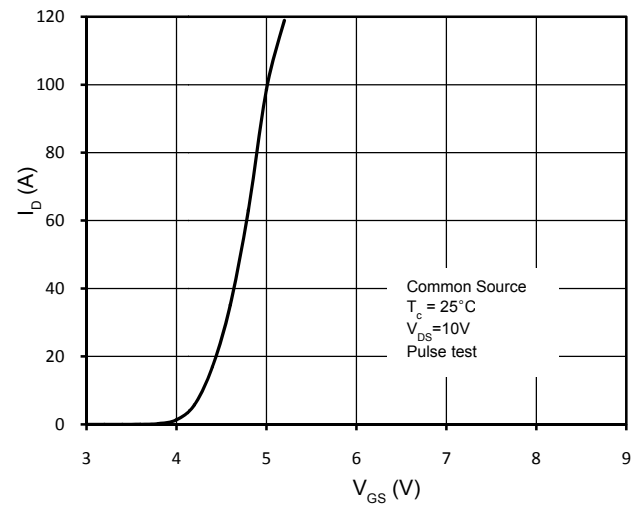


Figure 2. Transfer Characteristics

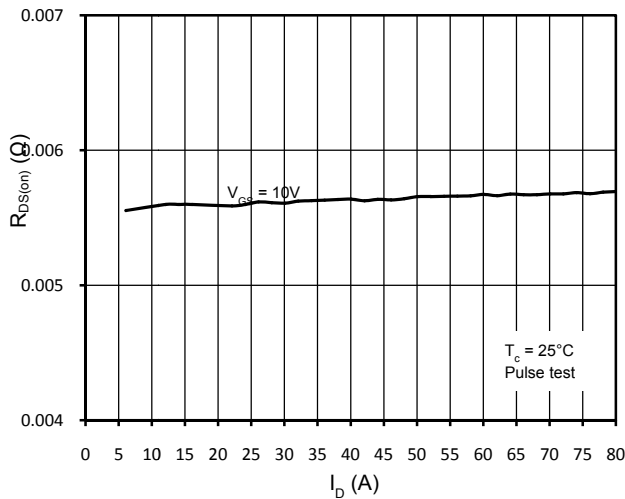


Figure 3. Static Drain-Source On Resistance

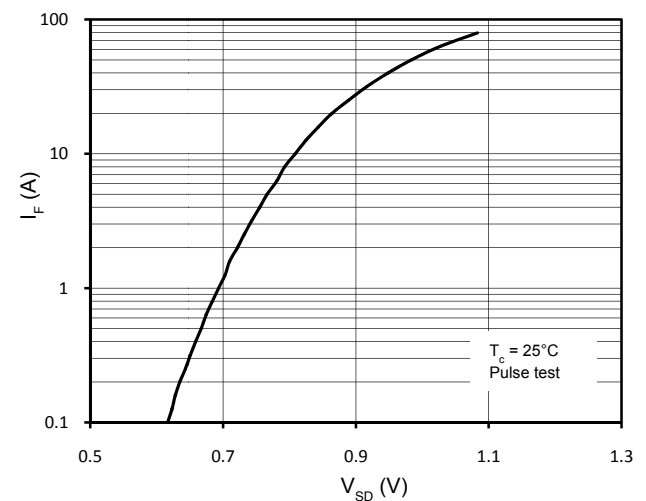
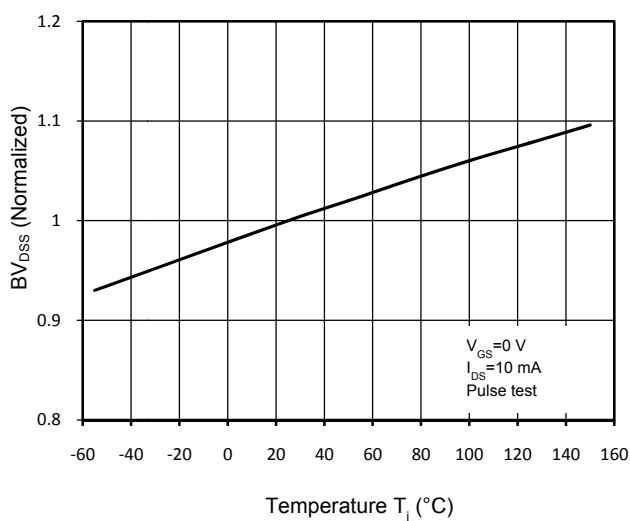
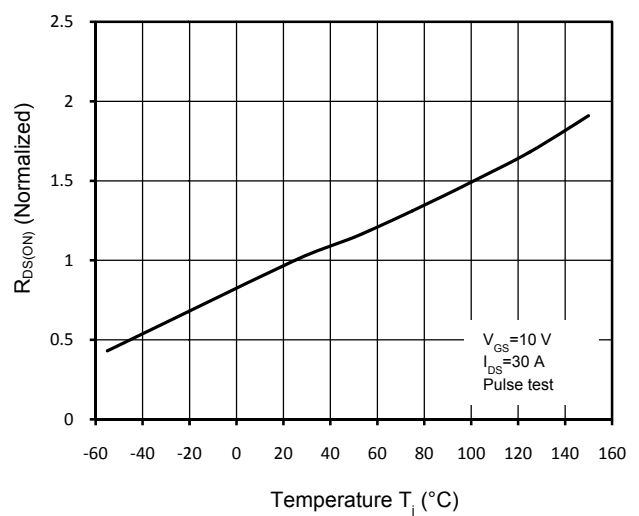


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DS} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

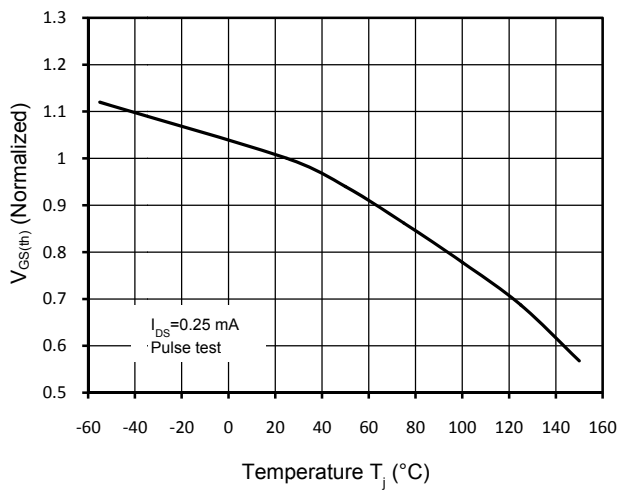


Figure 7. Threshold Voltage vs. Temperature

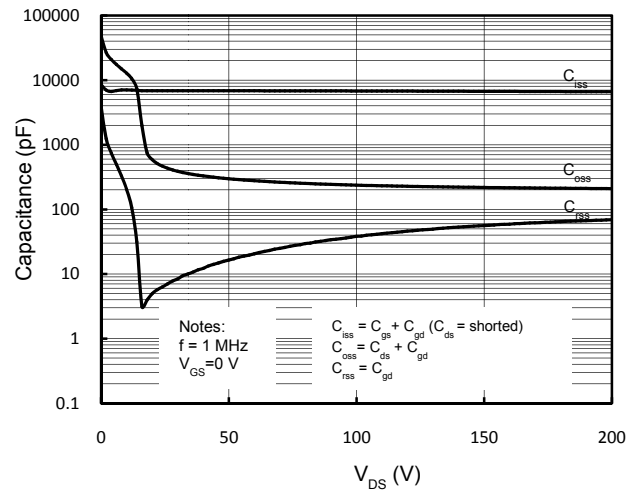


Figure 8. Capacitance Characteristics

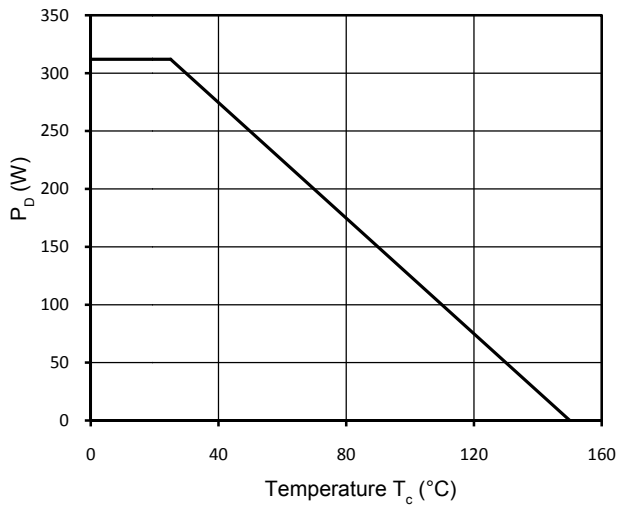


Figure 9. Power Dissipation

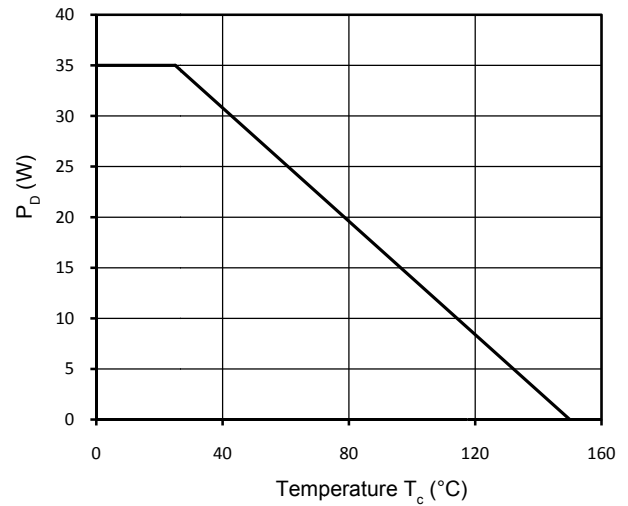


Figure 10. Power Dissipation (TO-220F)

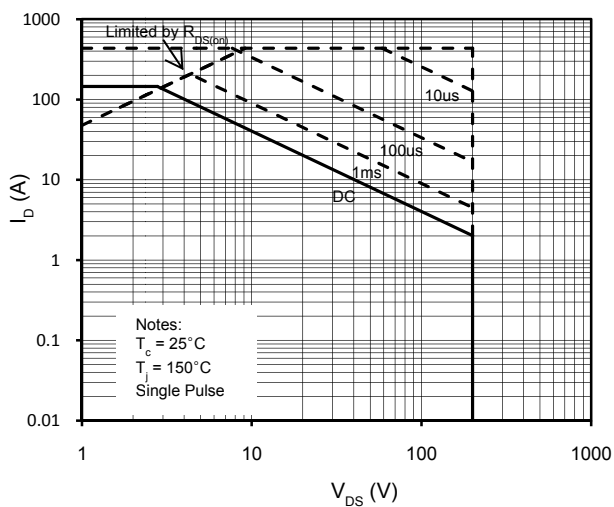


Figure 11. Maximum Safe Operating Area

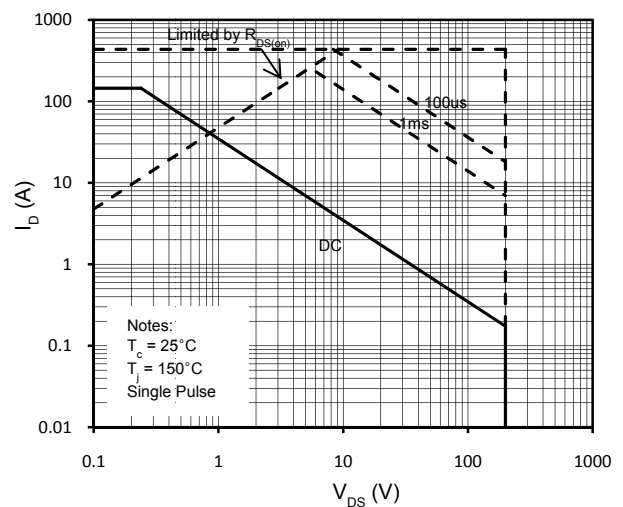


Figure 12. Maximum Safe Operating Area (TO-220F)

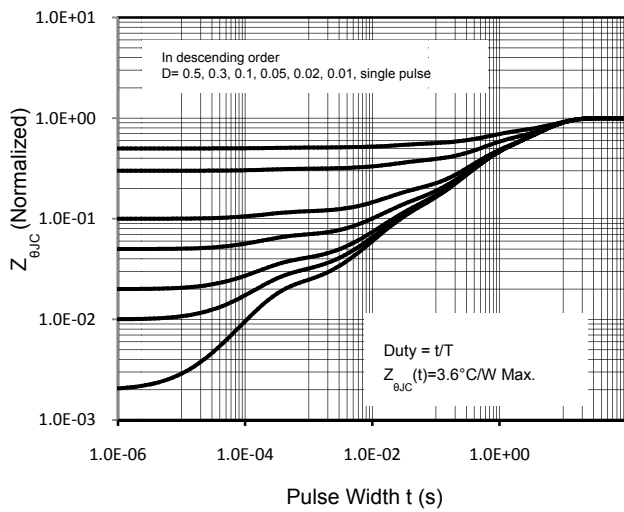


Figure 13. Transient Thermal Response Curve (TO-220F)

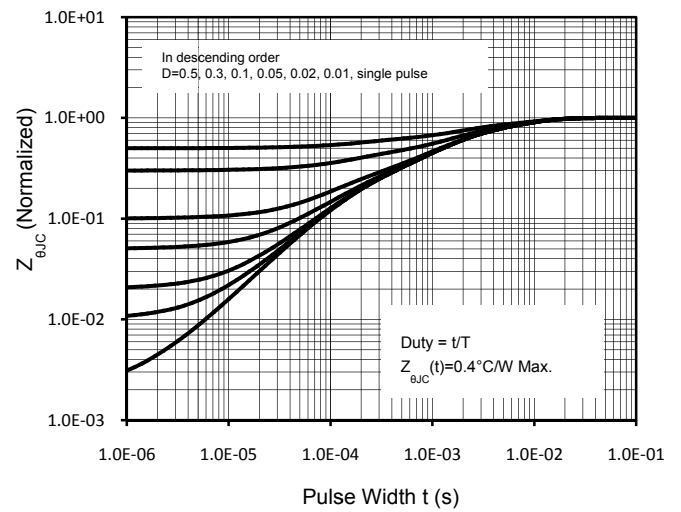


Figure 14. Transient Thermal Response Curve

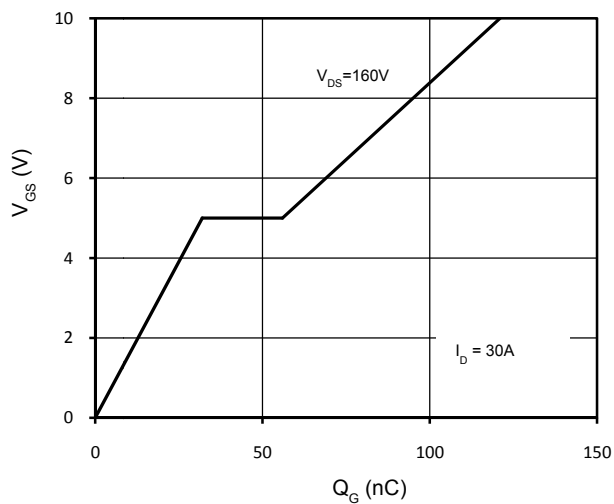
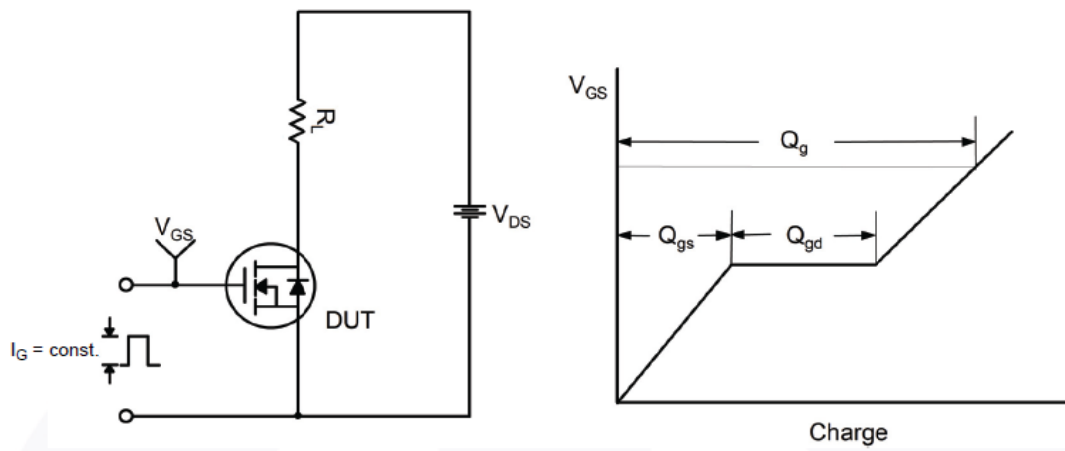
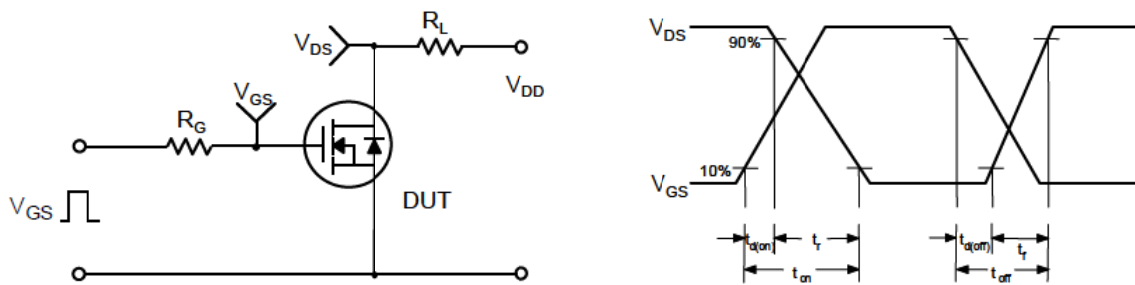


Figure 15. Gate Charge Characteristics

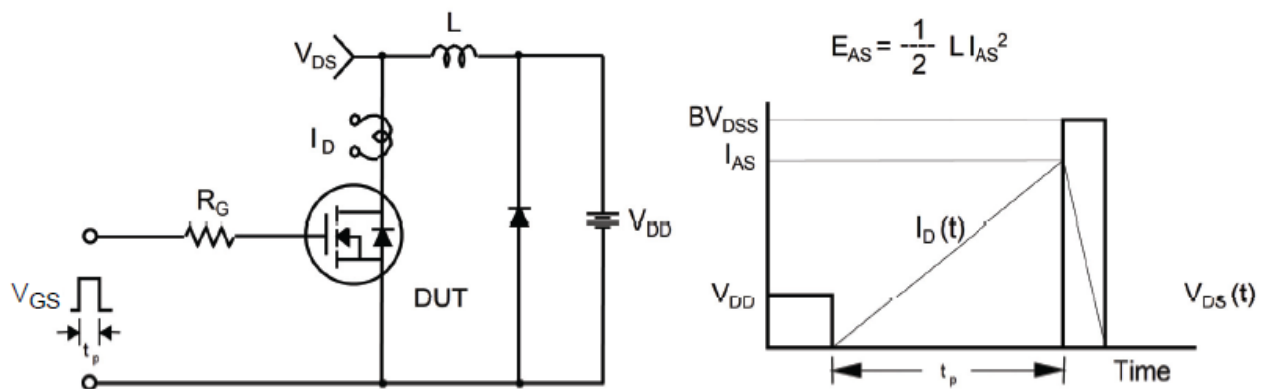
Gate Charge Test Circuit & Waveform



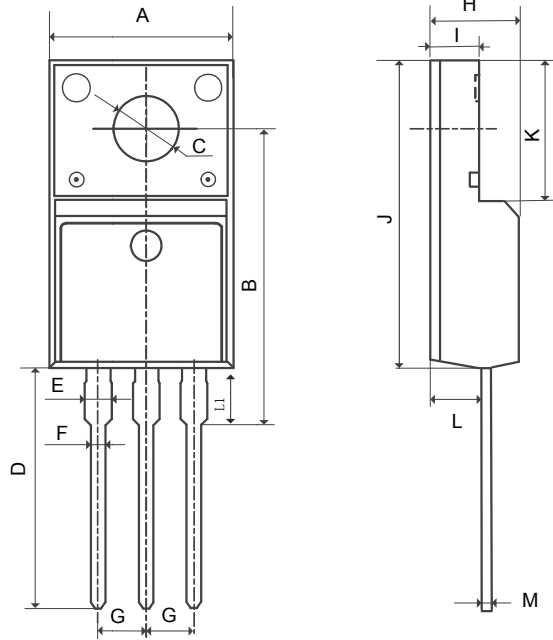
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220F

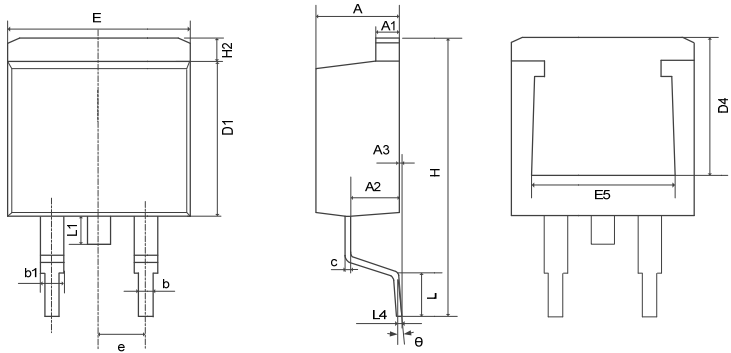


COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-263

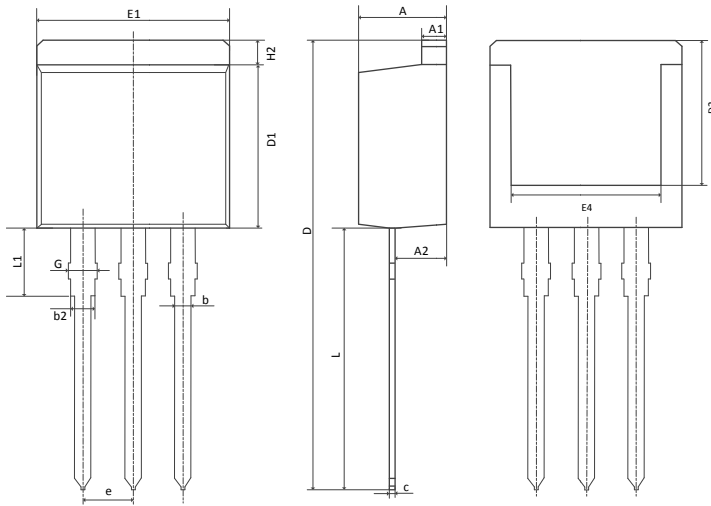
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.19	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.60
D1	8.45	9.35
D4	6.60	—
E	9.80	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	16.00
H2	1.07	1.47
L	2.00	2.70
L1	1.15	1.75
L4	0.25BSC	
θ	0°	9°

Mechanical Dimensions for TO-262

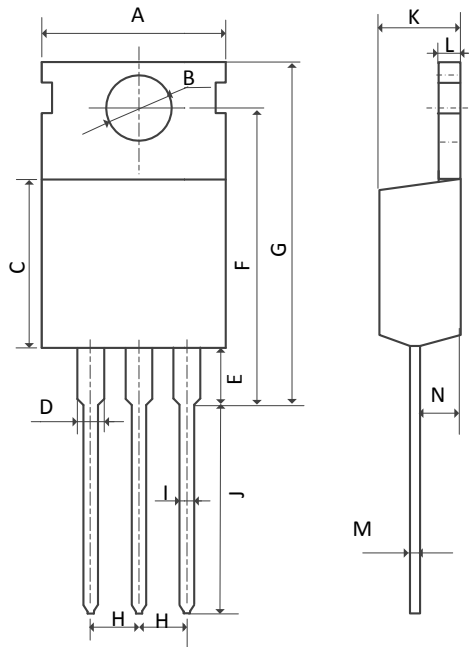
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.2	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.6
D	22.00	24.02
D1	8.45	9.3
D2	6.00	—
E1	9.8	10.40
E4	7.06	—
e	2.54BSC	
G	1.23	1.50
H2	—	1.50
L	12.90	14.16
L1	2.80	4.00

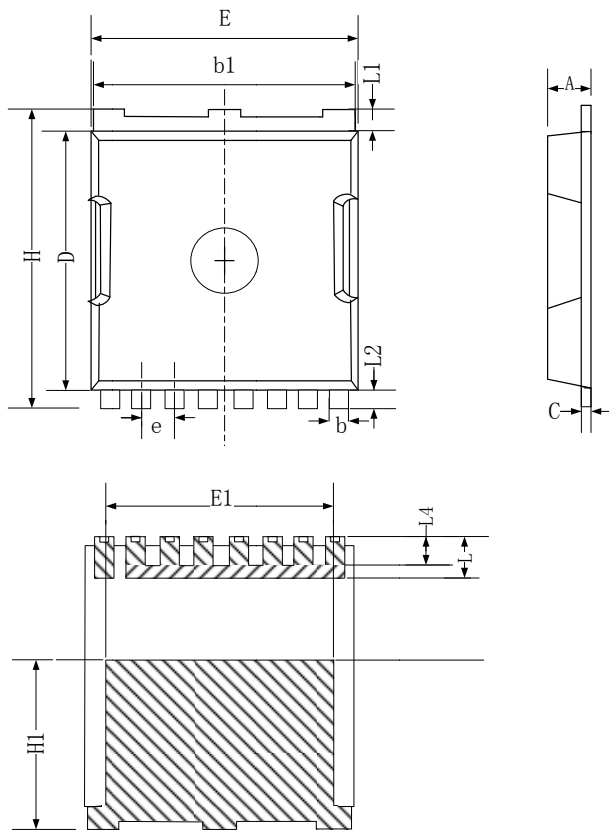
Mechanical Dimensions for TO-220

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.90
G	19.60MAX	
H	2.54REF	
I	0.70	0.95
J	9.25	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Mechanical Dimensions for TO-LL

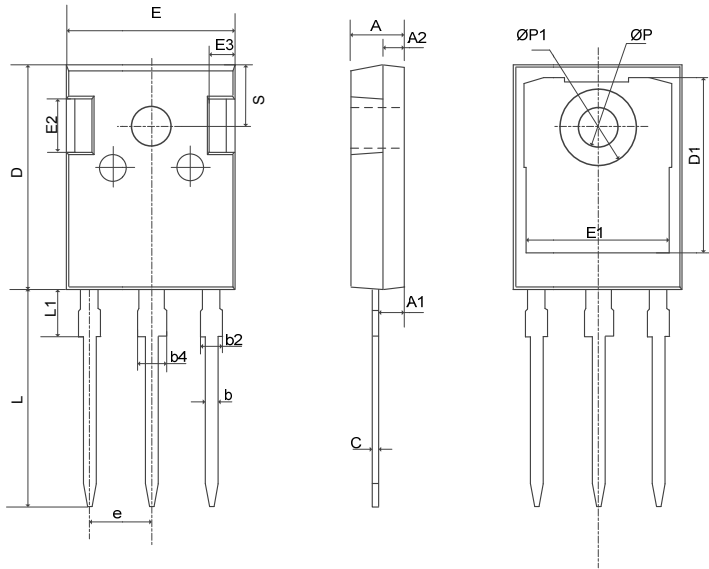


COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	2.15	2.45
b	0.7	0.95
b1	9.6	9.95
C	0.4	0.6
D	10.1	10.6
E	9.6	10.1
E1	7.9	8.5
e	1.20BSC	
H	11.38	11.88
H1	6.65	7.2
L	1.4	2
L1	0.5	0.9
L2	0.48	0.72
L4	1	1.3

Mechanical Dimensions for TO-247

COMMON DIMENSIONS

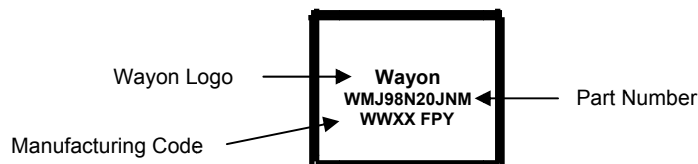


SYMBOL	MM	
	MIN	MAX
A	4.80	5.21
A1	2.21	2.61
A2	1.85	2.16
b	1.07	1.36
b2	1.91	2.41
b4	2.87	3.38
c	0.51	0.75
D	20.70	21.30
D1	16.25	17.65
E	15.50	16.13
E1	12.38	13.60
E2	3.68	5.20
E3	1.00	2.70
e	5.44BSC	
L	19.62	20.32
L1	—	4.40
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

Ordering Information

Part	Package	Marking	Packing method
WML98N20JNM	TO-220F	WML98N20JNM	Tube
WMK98N20JNM	TO-220	WMK98N20JNM	Tube
WMN98N20JNM	TO-262	WMN98N20JNM	Tube
WMM98N20JNM	TO-263	WMM98N20JNM	Tape and Reel
WMLL98N20JNM	TO-LL	WMLL98N20JNM	Tape and Reel
WMJ98N20JNM	TO-247	WMJ98N20JNM	Tube

Marking Information



Contact Information

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201202

Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

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